

# RT1P430X SERIES

Transistor

Transistor With Resistor

For Switching Application

Silicon PNP Epitaxial Type

## DESCRIPTION

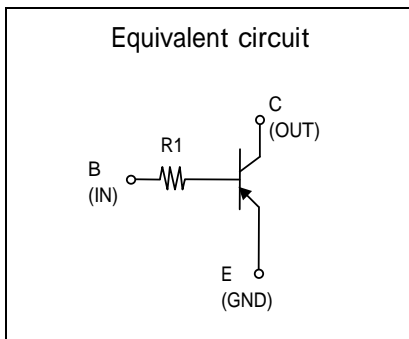
RT1P430X is a one chip transistor with built-in bias resistor, NPN type is RT1N430X.

## FEATURE

- Built-in bias resistor (R1=4.7k ).

## APPLICATION

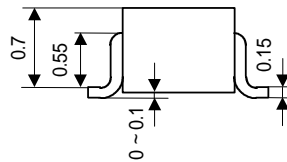
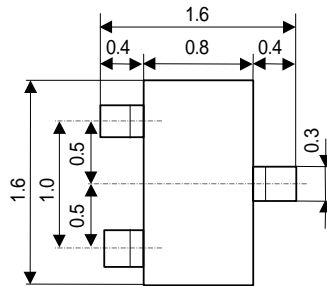
Inverted circuit, switching circuit, interface circuit, driver circuit.



## OUTLINE DRAWING

UNIT : mm

RT1P430U



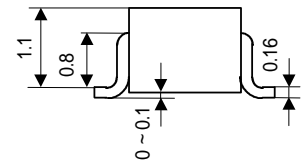
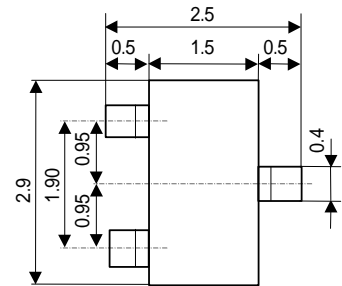
JEITA: -

JEDEC: -

Terminal Connector

- : Base
- : Emitter
- : Collector

RT1P430C



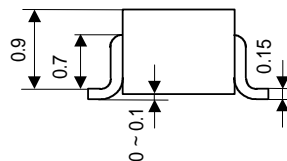
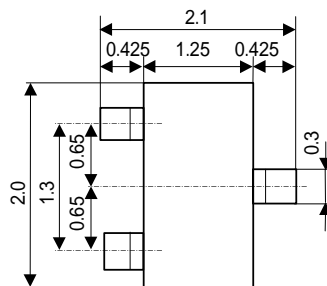
JEITA: SC-59

JEDEC: Similar to TO-236

Terminal Connector

- : Base
- : Emitter
- : Collector

RT1P430M



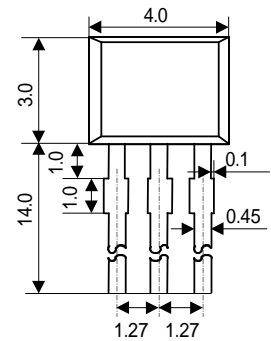
JEITA: SC-70

JEDEC: -

Terminal Connector

- : Base
- : Emitter
- : Collector

RT1P430S



JEITA: -

JEDEC: -

Terminal Connector

- : Emitter
- : Collector
- : Base

# RT1P430X SERIES

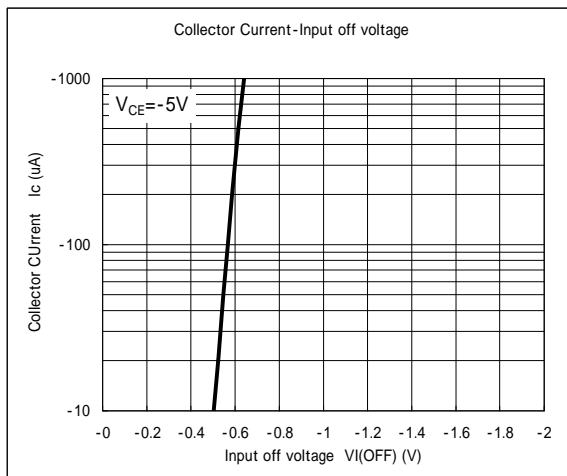
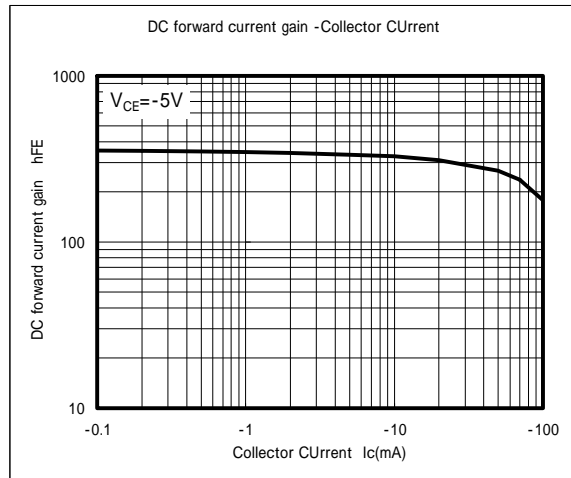
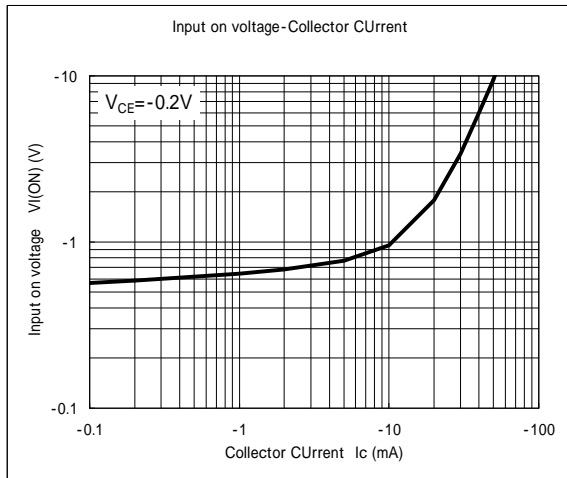
Transistor With Resistor  
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## MAXIMUM RATING (Ta=25 )

| SYMBOL    | PARAMETER                     | RATING     |          |            |          | UNIT |
|-----------|-------------------------------|------------|----------|------------|----------|------|
|           |                               | RT1P430U   | RT1P430M | RT1P430C   | RT1P430S |      |
| $V_{CBO}$ | Collector to Base voltage     | -50        |          |            |          | V    |
| $V_{EBO}$ | Emitter to Base voltage       | -6         |          |            |          | V    |
| $V_{CEO}$ | Collector to Emitter voltage  | -50        |          |            |          | V    |
| $I_C$     | Collector current             | -100       |          |            |          | mA   |
| $I_{CM}$  | Peak Collector current        | -200       |          |            |          | mA   |
| $P_C$     | Collector dissipation(Ta=25 ) | 150        | 200      | 450        | mW       |      |
| $T_j$     | Junction temperature          | +150       | +150     |            |          |      |
| $T_{stg}$ | Storage temperature           | -55 ~ +150 |          | -55 ~ +150 |          |      |

## ELECTRICAL CHARACTERISTICS (Ta=25 )

| SYMBOL        | PARAMETER                 | TEST CONDITION               | LIMIT |     |      | UNIT    |
|---------------|---------------------------|------------------------------|-------|-----|------|---------|
|               |                           |                              | MIN   | TYP | MAX  |         |
| $V_{(BR)CEO}$ | C to E break down voltage | $I_C = -100 \mu A, R_{BE} =$ | -50   |     |      | V       |
| $I_{CBO}$     | Collector cut off current | $V_{CB} = -50V, I_E = 0$     |       |     | -0.1 | $\mu A$ |
| $h_{FE}$      | DC forward current gain   | $V_{CE} = -5V, I_C = -1mA$   | 100   |     |      | -       |
| $V_{CE(sat)}$ | C to E saturation voltage | $I_C = -10mA, I_B = -0.5mA$  |       |     | -0.3 | V       |
| $R_1$         | Input resistance          |                              | 3.3   | 4.7 | 6.1  | k       |
| $f_T$         | Gain band width product   | $V_{CE} = -6V, I_E = 10mA$   |       | 150 |      | MHz     |





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